Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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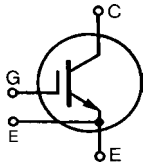
IXYS

HiPerFAST™ IGBT

IXGN 50N60B

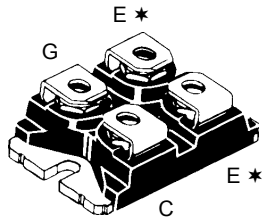
V_{CES} = 600 V
I_{C25} = 75 A
$V_{CE(sat)}$ = 2.3 V
$t_{fi(typ)}$ = 120ns

Preliminary data sheet



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	75	A
I_{C90}	T_C = 90°C	50	A
I_{CM}	T_C = 25°C, 1 ms	200	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load, L = 30 µH	I_{CM} = 100 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	300	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
V_{isol}	RMS, t = 1 minute, 50/60 Hz	2500	V
Weight		30	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C

SOT-227B miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
✶ Either emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package SOT-227B
- Aluminium nitride isolation - high power dissipation
- Isolation voltage 3000 V~
- Very high current, fast switching IGBT
- Low $V_{CE(sat)}$ for minimum on-state conduction losses
- MOS Gate turn-on drive simplicity
- Low collector-to-case capacitance (< 50 pF)
- Low package inductance (< 5 nH) - easy to drive and to protect

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		2.5		5	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	 T_J = 125°C			200 1	µA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				2.3	V

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Easy to mount with 2 screws
- Space savings
- High power density

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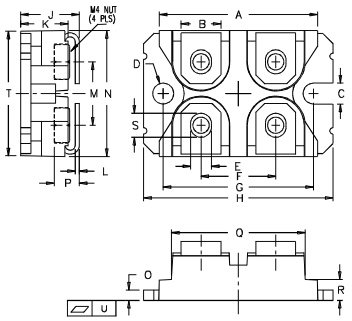
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	25	42		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		4100		pF
C_{oes}			310		pF
C_{res}			95		pF
Q_G	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		160		nC
Q_{GE}			30		nC
Q_{GC}			55		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		50		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		50		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 2.7 Ω		150	250	ns
t_{fi}	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		120	250	ns
E_{off}			3	4.5	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		50		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		60		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 2.7 Ω		3		mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		200		ns
t_{fi}			250		ns
E_{off}			4.2		mJ
R_{thJC}				0.42	K/W
R_{thCK}			0.05		K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Figure 1. Saturation Voltage Characteristics

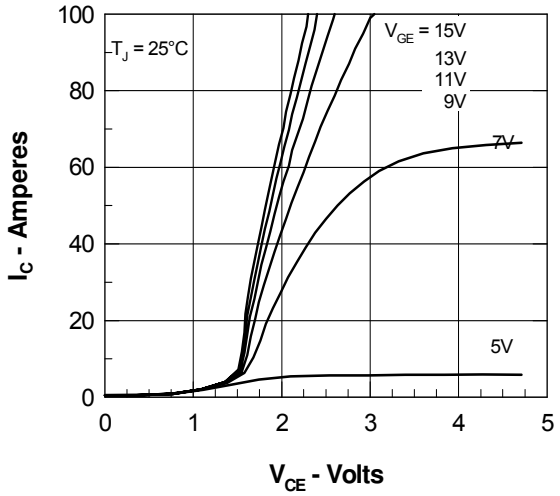


Figure 2. Extended Output Characteristics

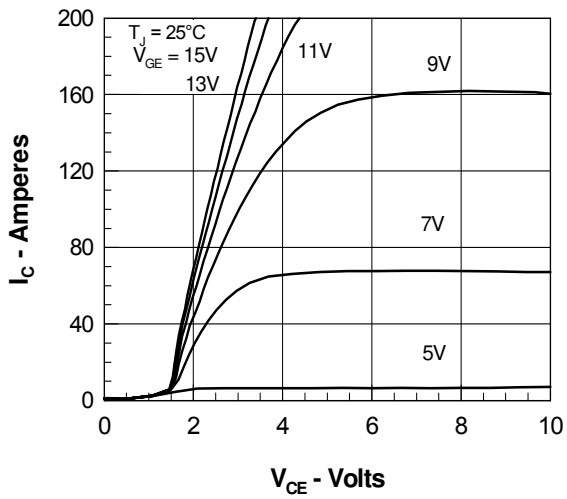


Figure 3. Saturation Voltage Characteristics

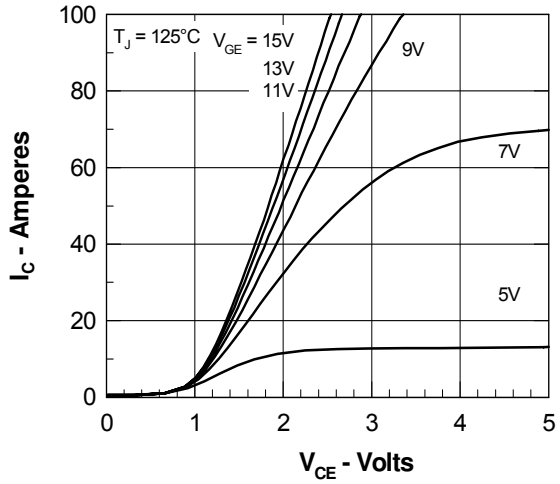


Figure 4. Temperature Dependence of $V_{CE(sat)}$

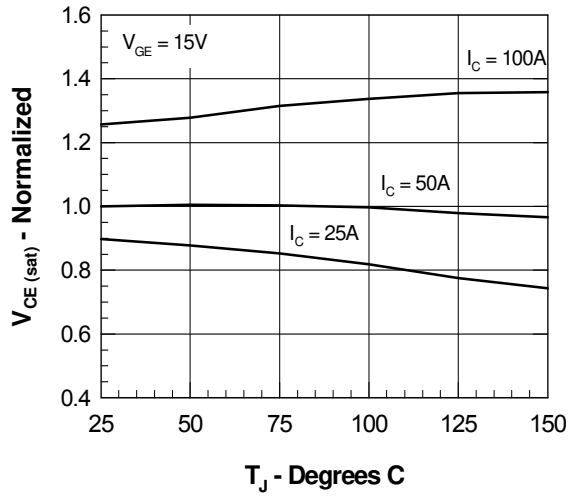


Figure 5. Admittance Curves

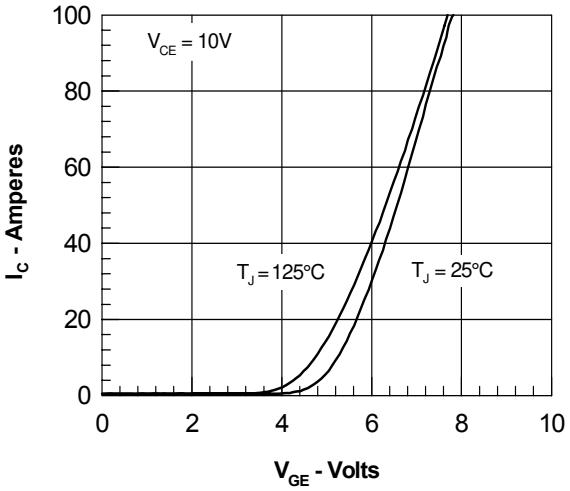


Figure 6. Capacitance Curves

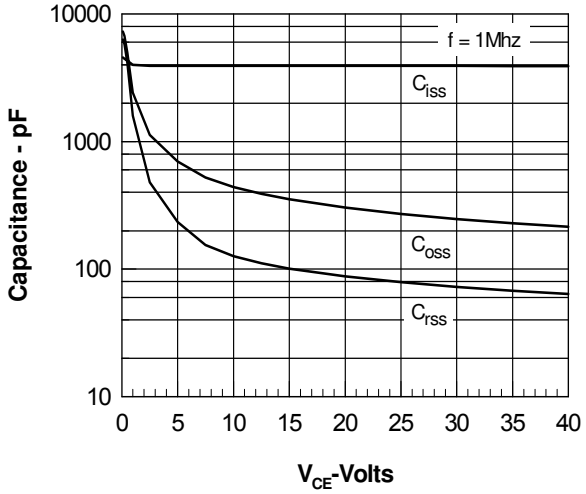


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Figure 7. Dependence of E_{ON} and E_{OFF} on I_C

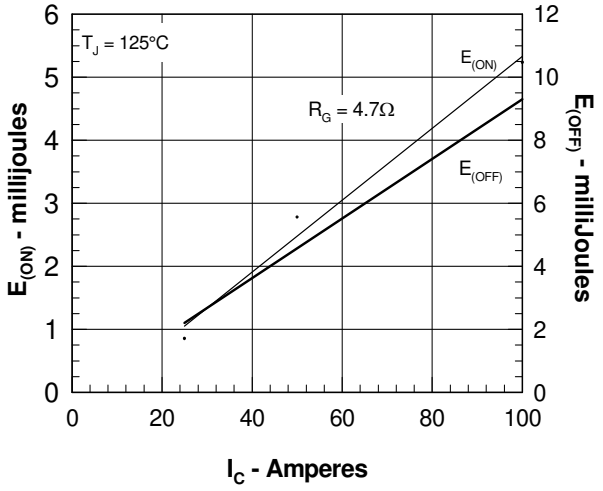


Figure 8. Dependence of E_{ON} and E_{OFF} on R_G

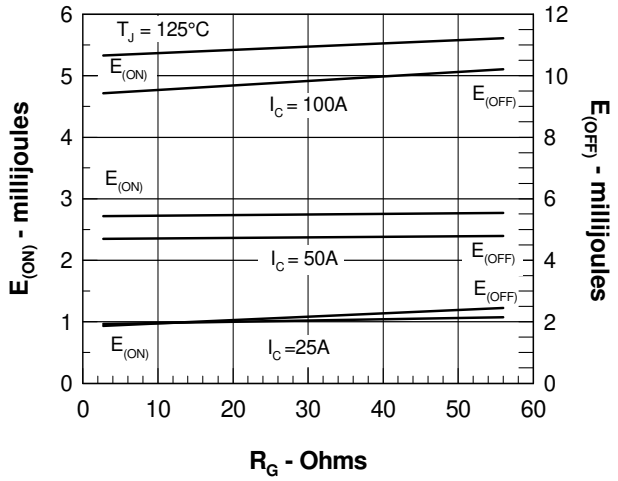


Figure 9. Gate Charge

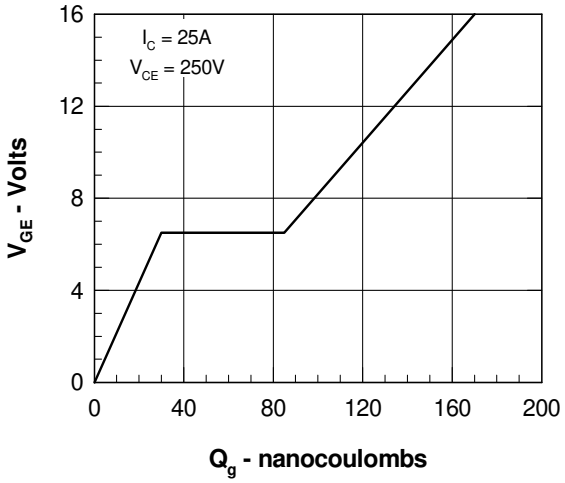


Figure 10. Turn-off Safe Operating Area

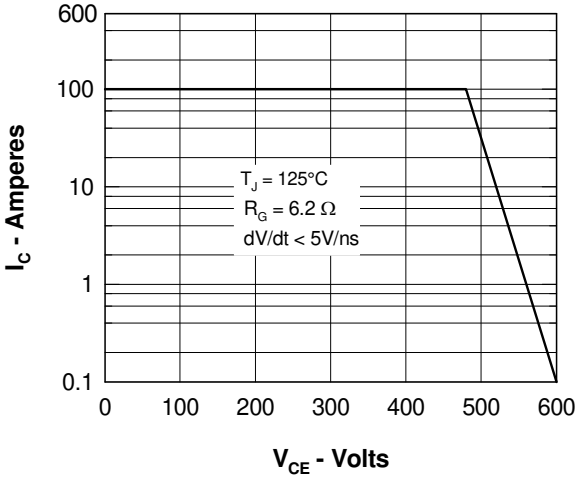
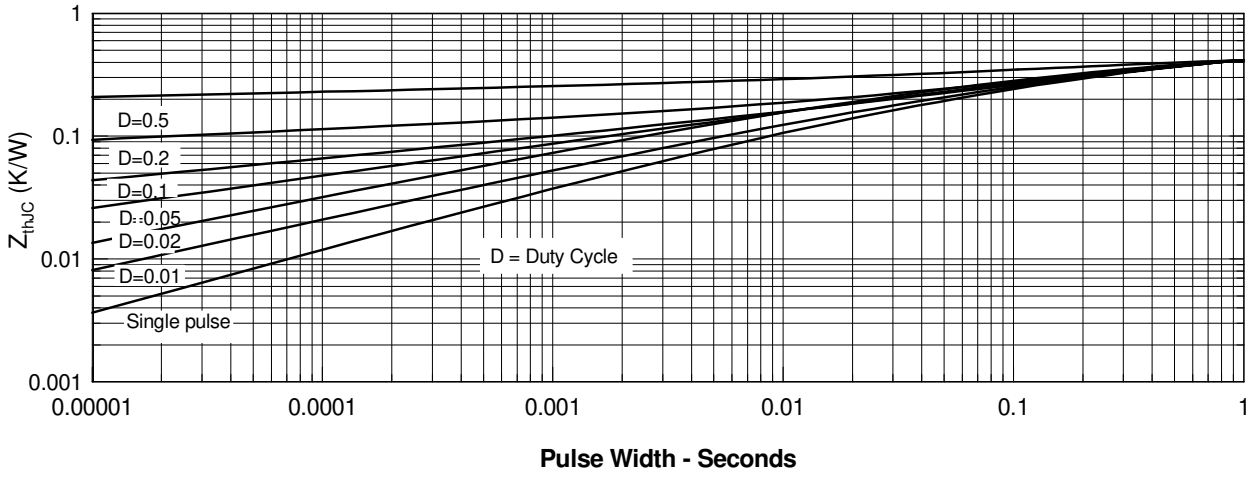


Figure 11. IGBT Transient Thermal Resistance



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